

330mW Stereo Audio Power Amp With Shutdown

Features

- Operating voltage: 2.4V~6.0V
- Very low standby current 0.5μA (Typ.)
- · High signal-to-noise ratio
- · High slew rate
- Output power 330mW at 10% THD+N into 8Ω
- · Excellent power supply ripple rejection

- Low power consumption
- Wide temperature operating range
- · Direct drive speaker
- · Shutdown function
- · 8-pin SOP package

Applications

- CD ROM DVD player
- · Notebook/Desktop PC
- · Portable Audio Device

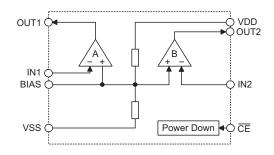
- · Headphone Amplifier
- · Microphone Pre-amplifier
- Discman/MP3

General Description

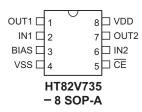
HT82V735 is a class AB stereo earphone driver designed for portable digital audio application. Pin assignments and application circuits are compatible with LM4880 which is suitable for effective low cost applications. The HT82V735 can deliver a maximum of 330mW

Output power to an 8Ω load with less than 10% (THD+N) from a 5V power supply. The very low standby current in shutdown mode contributes to the reduction of power consumption of battery-powered equipments. It provides 8-SOP package.

Block Diagram



Pin Assignment



Pin Description

Pin No.	Pin Name	I/O	Description		
1	OUT1	0	Channel 1 output pin		
2	IN1	1	Channel 1 Audio input		
3	BIAS	ı	Supports a voltage driver for internal bias		
4	VSS	_	egative power supply, ground		
5	CE	1	ower down mode when held high, I (power down) =1µA		
6	IN2	1	hannel 2 Audio input		
7	OUT2	0	Channel 2 output pin		
8	VDD	_	Positive power supply		



Absolute Maximum Ratings

Supply VoltageV _{SS} -0.3V to V _{SS} +6V	Storage Temperature50°C to 125°C
Input VoltageV _{SS} -0.3V to V _{DD} +0.3V	Operating Temperature–20°C to 70°C

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

Electrical Characteristics

 V_{SS} =0V; f_i =1kHz; R_L =32 Ω ; Ta=25 $^{\circ}$ C

C	Demonstration	Test Conditions			_			
Symbol	Parameter	V_{DD}	Conditions	Min.	Тур.	Max.	Unit	
Supplies								
V_{DD}	Supply Voltage	_	_	2.4	_	6	V	
I _{DD}	Supply Current	5V	No load	_	10		mA	
I _{PD}	Power-down Current	5V	_	_	1	_	μА	
D.C. Charac	cteristics							
V _{I(OS)}	Input Offset Voltage	5V	_	_	10	_	mV	
Io	Maximum Output Current	5V	(THD+N)/S<0.1%	_	62		mA	
Ro	Output Resistance	5V	_	_	230	_	mΩ	
			R _L =8Ω	0.66	_	3	V	
Vo	Output Voltage Swing	5V	R _L =16Ω	0.38	_	3.15	V	
			R _L =32Ω	0.18	_	3.29	V	
PSRR	Power Supply Rejection Ratio		$C_S = 2.2 \mu F, \\ V_{RIPPLE} = 200 V_{RMS}, \\ f = 120 Hz$	_	66	_	dB	
X _{TALK}	Channel Separation	5V	$\begin{aligned} & \text{P}_{\text{O}}\text{=}200\text{mW}, \text{R}_{\text{L}}\text{=}8\Omega, \\ & \text{C}_{\text{B}}\text{=}2.2\mu\text{F} \end{aligned}$	_	85	_	dB	
A.C. Charac	cteristics							
(THD+N)/S	Total Harmonic Distortion Plus Noise to Signal Ratio	5V	P_O =200mW, R_L =8 Ω , f=1kHz	_	0.03	_		
			P_O =120mW, R_L =16 Ω , f=1kHz	_	0.01	_	%	
			P_O =75mW, R_L =32 Ω , f=1kHz	_	0.01	_		
		3.3V	P_O =30mW, R_L =32 Ω , f=1kHz	_	0.01	_		
			(THD+N)/S=0.1%, f=1kHz	_	_	_		
			R _L =8Ω	_	240	_		
			R _L =16Ω	_	160	_		
D	0.41.		R _L =32Ω	_	90	_		
P _O	Output Power	5V	(THD+N)/S=10%, f=1kHz	_	_	_	mW 	
			R _L =8Ω	_	330	_		
			R _L =16Ω	_	200	_		
			R _L =32Ω		110	_		

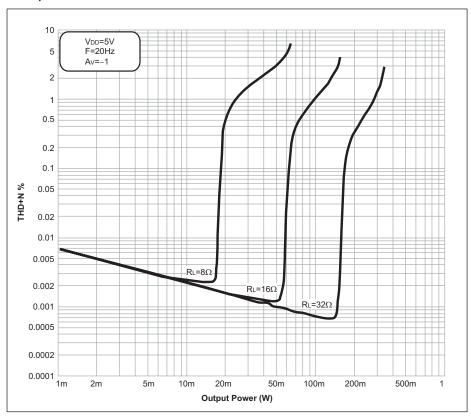
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Symbol	Parameter		Test Conditions		Trees	Max.	Unit
Syllibol	Farameter	V_{DD}	Conditions	Min.	Тур.	wax.	Onit
S/N	Signal to Noise Ratio	5V	V_{IN} =1 $_{VRMS}$, R_L =8 Ω		92	_	dB
SR	Slew Rate	5V	_	_	3	_	V/μs
ATT	Power-down Attenuation		1kHz, 0dB	_	70	_	dB

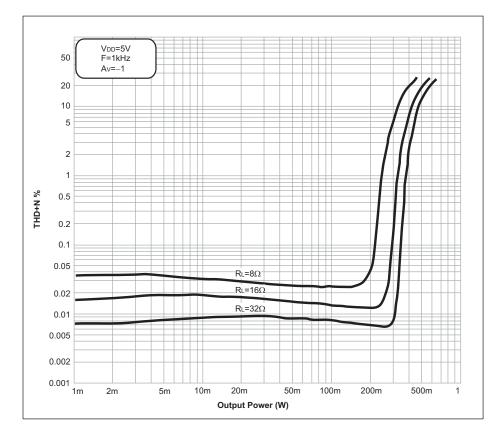
Typical Performance Characteristics

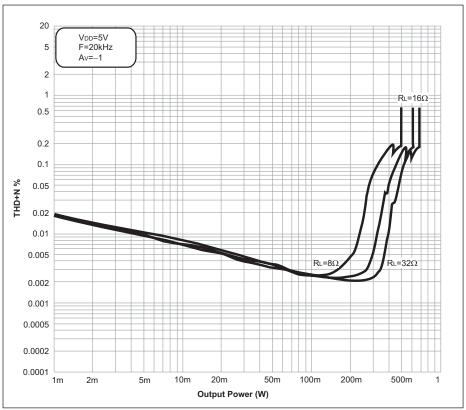
THD+N vs. Output Power



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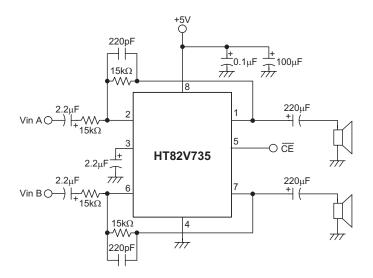








Application Circuits

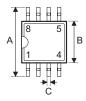


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Package Information

8-pin SOP (150mil) Outline Dimensions





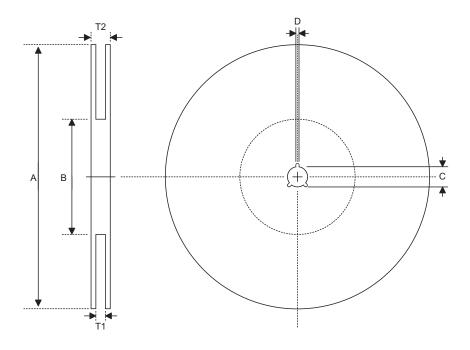


Cymphal	Dimensions in mil					
Symbol	Min.	Nom.	Max.			
А	228	_	244			
В	149	_	157			
С	14	_	20			
C'	189	_	197			
D	53	_	69			
E	_	50	_			
F	4	_	10			
G	22	_	28			
Н	4	_	12			
α	0°	_	10°			



Product Tape and Reel Specifications

Reel Dimensions

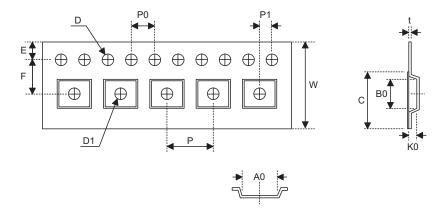


SOP 8N

Symbol	Description	Dimensions in mm
Α	Reel Outer Diameter	330±1.0
В	Reel Inner Diameter	62±1.5
С	Spindle Hole Diameter	13.0+0.5 -0.2
D	Key Slit Width	2.0±0.5
T1	Space Between Flange	12.8+0.3 -0.2
T2	Reel Thickness	18.2±0.2



Carrier Tape Dimensions



SOP 8N

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	12.0+0.3 -0.1
Р	Cavity Pitch	8.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	5.5±0.1
D	Perforation Diameter	1.55±0.1
D1	Cavity Hole Diameter	1.5+0.25
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.1
A0	Cavity Length	6.4±0.1
В0	Cavity Width	5.20±0.1
K0	Cavity Depth	2.1±0.1
t	Carrier Tape Thickness	0.3±0.05
С	Cover Tape Width	9.3



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